

## 1. General description

Planar passivated SCR with sensitive gate in a SOT223 (SC-73) surface mountable plastic package. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

## 3. Applications

- Adapters
- Battery powered applications
- Industrial automation

## 4. Quick reference data

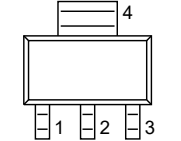

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{sp} \leq 112\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	0.6	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{sp} \leq 112\text{ °C}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	1	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	10	A
		half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	-	11	A
$T_j$	junction temperature	<a href="#">[1]</a>	-	-	125	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	50	200	μA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 14</a>	-	50	-	V/μs

[1] Operation above 110°C may require the use of a gate to cathode resistor of 1kΩ or less.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>SC-73 (SOT223)</p>	
2	A	anode		
3	G	gate		
4	mb	mb; connected to anode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT148W-600R	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

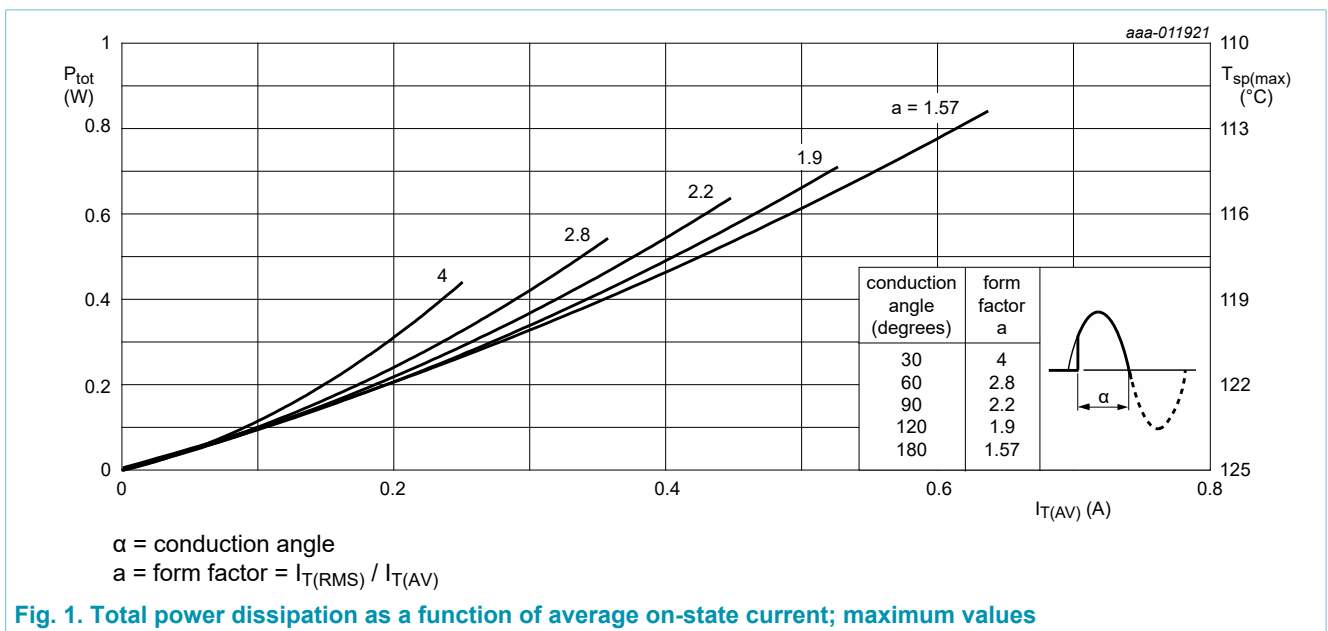
## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		[1]	-	600	V
$V_{RRM}$	repetitive peak reverse voltage			-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{sp} \leq 112\text{ }^{\circ}\text{C}$ ; Fig. 1		-	0.6	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{sp} \leq 112\text{ }^{\circ}\text{C}$ ; Fig. 2; Fig. 3		-	1	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 10\text{ ms}$ ; Fig. 4; Fig. 5		-	10	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 8.3\text{ ms}$		-	11	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN		-	0.5	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 400\text{ }\mu\text{A}$		-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current			-	1	A
$V_{RGM}$	peak reverse gate voltage			-	5	V
$P_{GM}$	peak gate power			-	1.2	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.12	W
$T_{stg}$	storage temperature			-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		[2]	-	125	$^{\circ}\text{C}$

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the thyristor may switch to the on-state.
- [2] Operation above 110°C may require the use of a gate to cathode resistor of 1kΩ or less.



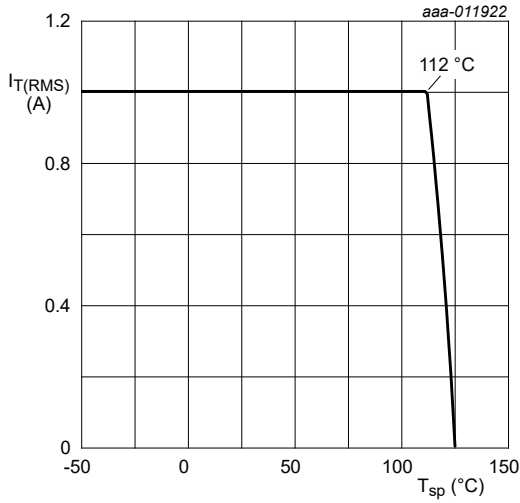


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

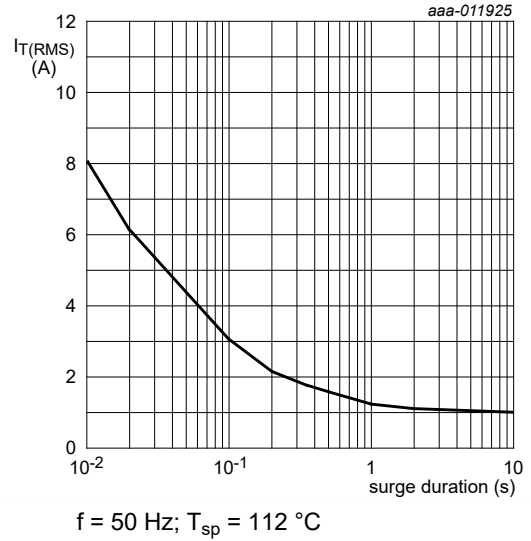


Fig. 3. RMS on-state current as a function of surge duration; maximum values

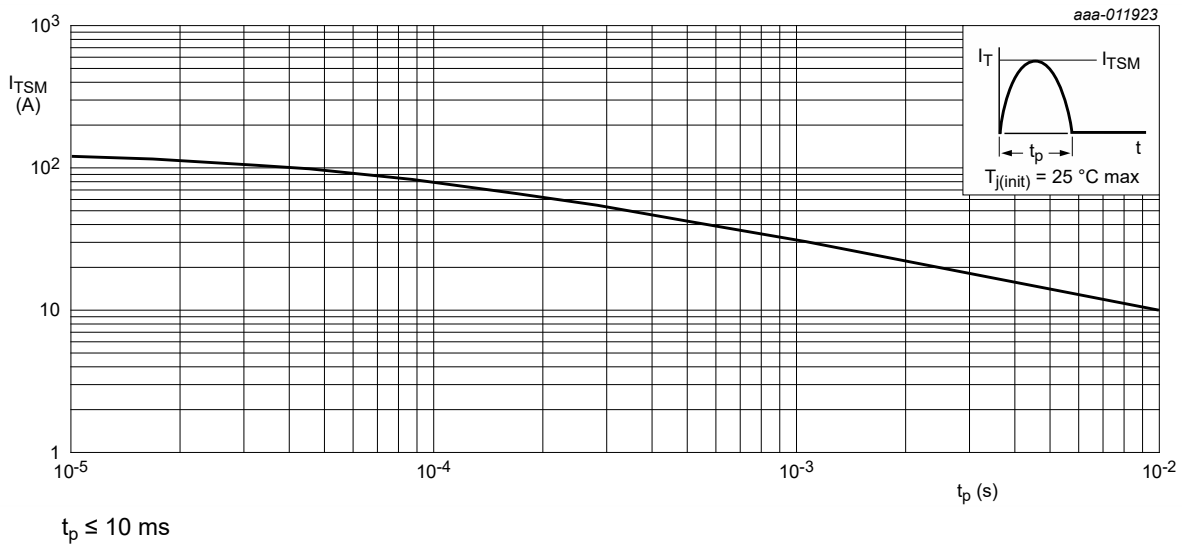


Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

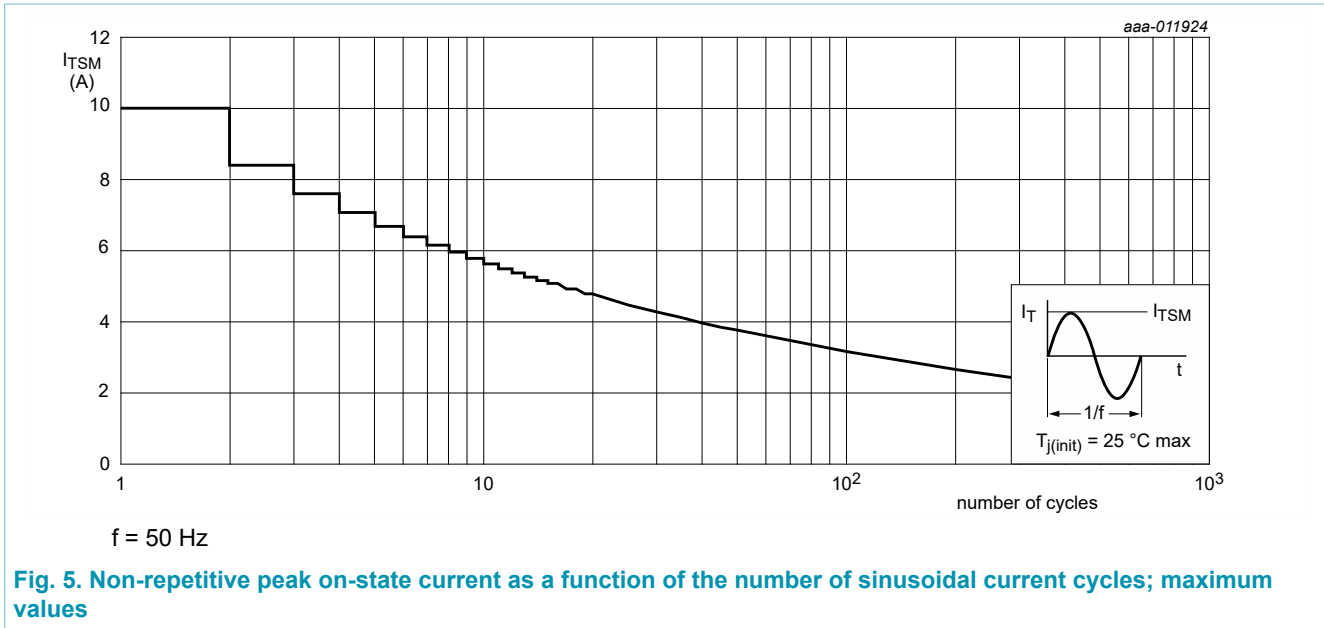


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	<a href="#">Fig. 6</a>	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; pad area; <a href="#">Fig. 7</a>	-	70	-	K/W
		printed circuit board mounted; minimum footprint; <a href="#">Fig. 8</a>	-	156	-	K/W

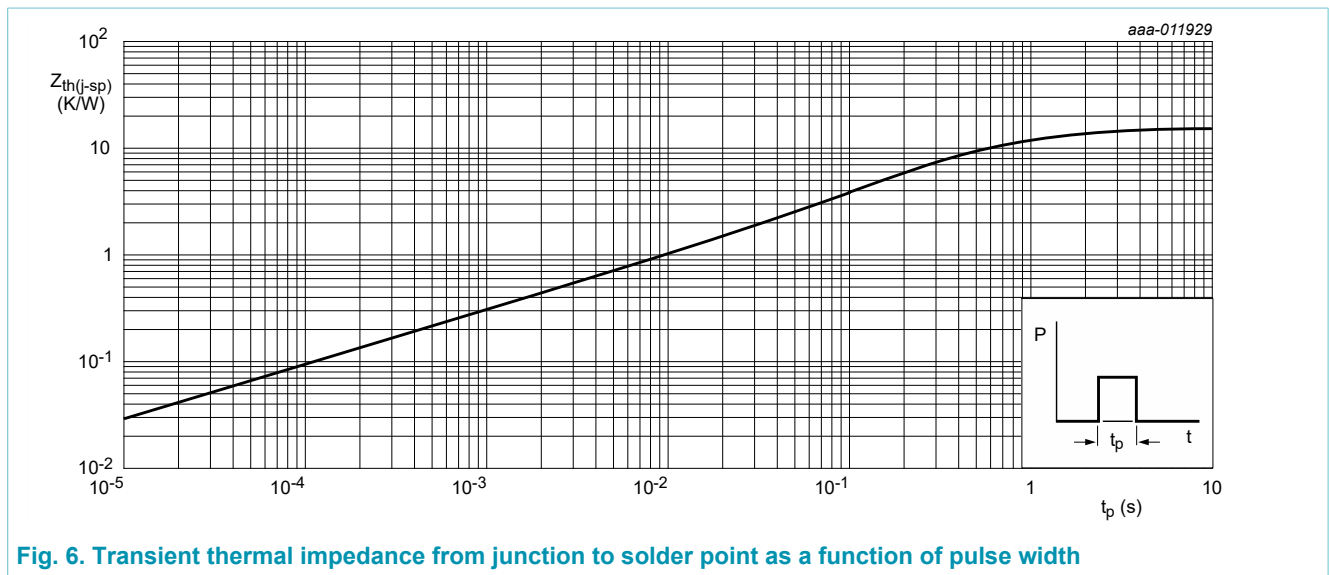
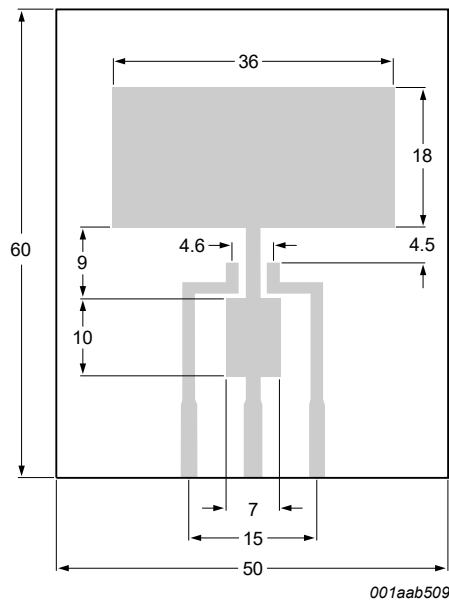
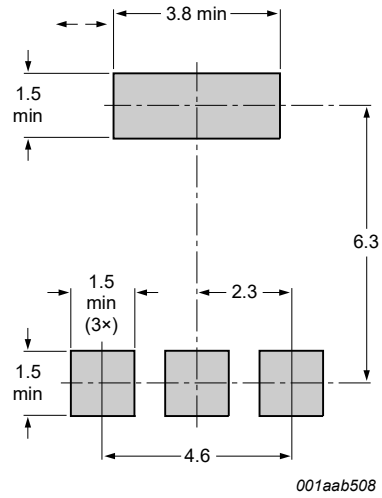


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm  
 Printed circuit board:  
 FR4 epoxy glass (1.6 mm thick), copper laminate  
 (35 um thick)

Fig. 7. Printed circuit board pad area: SOT223



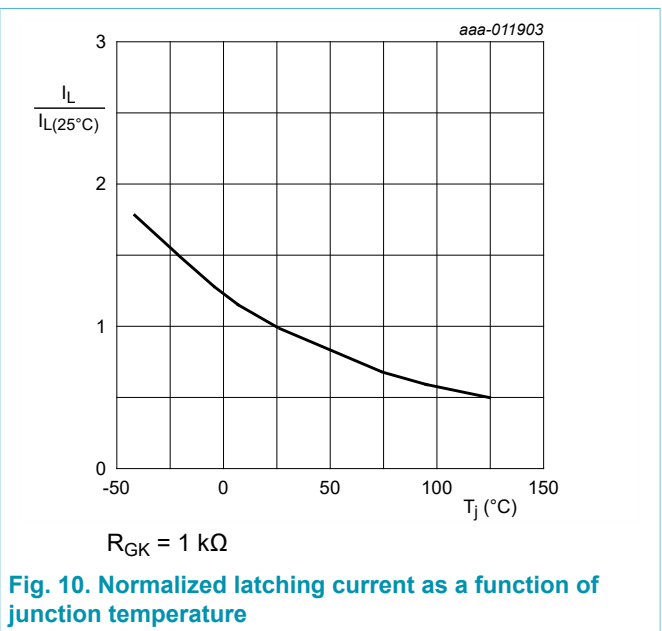
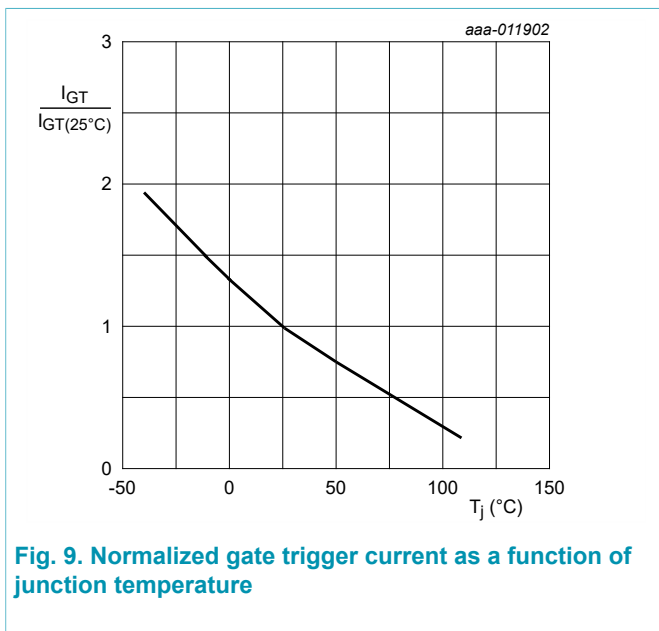
All dimensions are in mm

Fig. 8. Minimum footprint SOT223

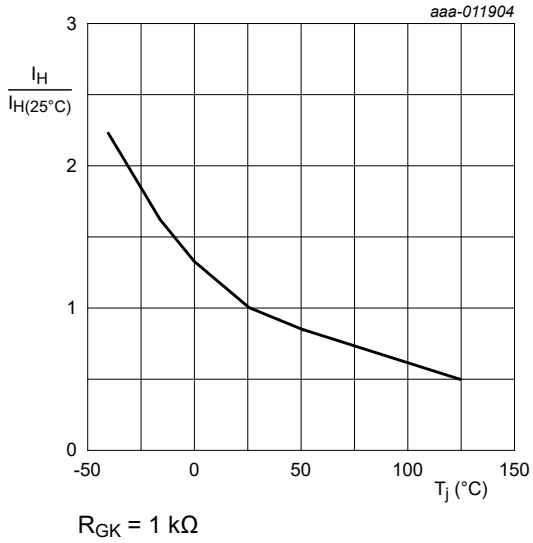
### 9. Characteristics

Table 6. Characteristics

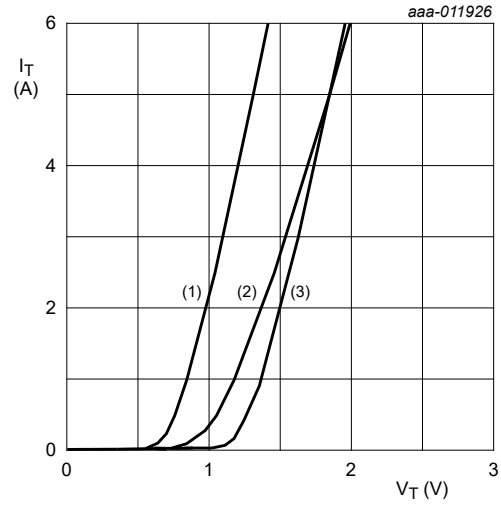
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9	-	50	200	$\mu\text{A}$
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10	-	0.17	10	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 11	-	0.1	6	mA
$V_T$	on-state voltage	$I_T = 2\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 12	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 13	-	0.4	1	V
		$V_D = 600\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C};$ Fig. 13	0.1	0.2	-	V
$I_D$	off-state current	$V_D = 600\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
$I_R$	reverse current	$V_R = 600\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 125\text{ }^\circ\text{C}; R_{GK} = 100\text{ }\Omega;$ ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; Fig. 14	-	50	-	$\text{V}/\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 4\text{ A}; V_D = 600\text{ V}; I_G = 5\text{ mA}; dI_G/dt = 0.2\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}$	-	2	-	$\mu\text{s}$
$t_q$	commutated turn-off time	$V_{DM} = 402\text{ V}; T_j = 125\text{ }^\circ\text{C}; I_{TM} = 4\text{ A}; V_R = 35\text{ V}; (dI_T/dt)_M = 30\text{ A}/\mu\text{s}; dV_D/dt = 2\text{ V}/\mu\text{s}; R_{GK(ext)} = 1\text{ k}\Omega; (V_{DM} = 67\%$ of $V_{DRM})$	-	100	-	$\mu\text{s}$







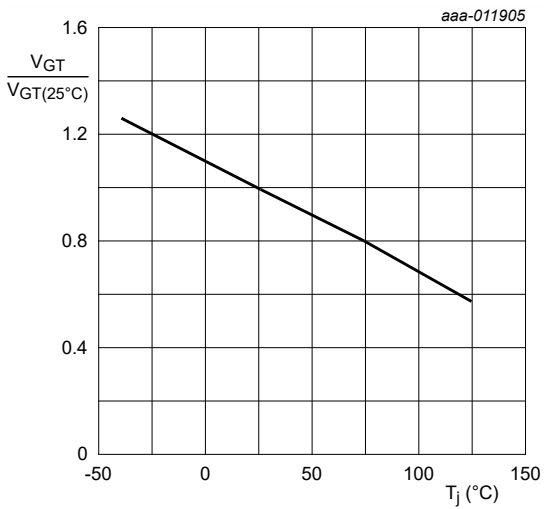
**Fig. 11. Normalized holding current as a function of junction temperature**



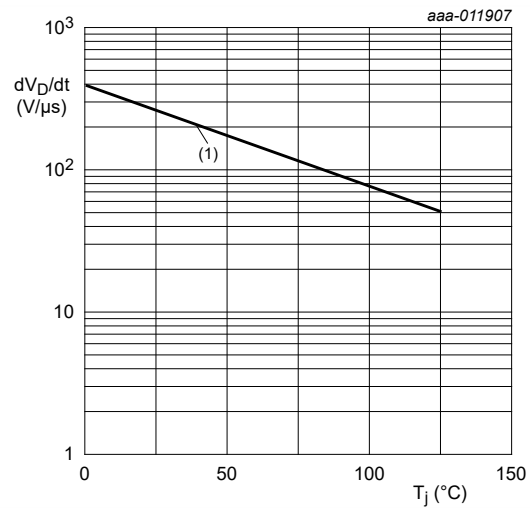
$V_o = 1.107 \text{ V}; R_s = 0.14 \Omega$

- (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 12. On-state current as a function of on-state voltage**



**Fig. 13. Normalized gate trigger voltage as a function of junction temperature**



(1)  $R_{GK} = 100 \Omega$

**Fig. 14. Critical rate of rise of off-state voltage as a function of junction temperature; typical values**

### 10. Package outline

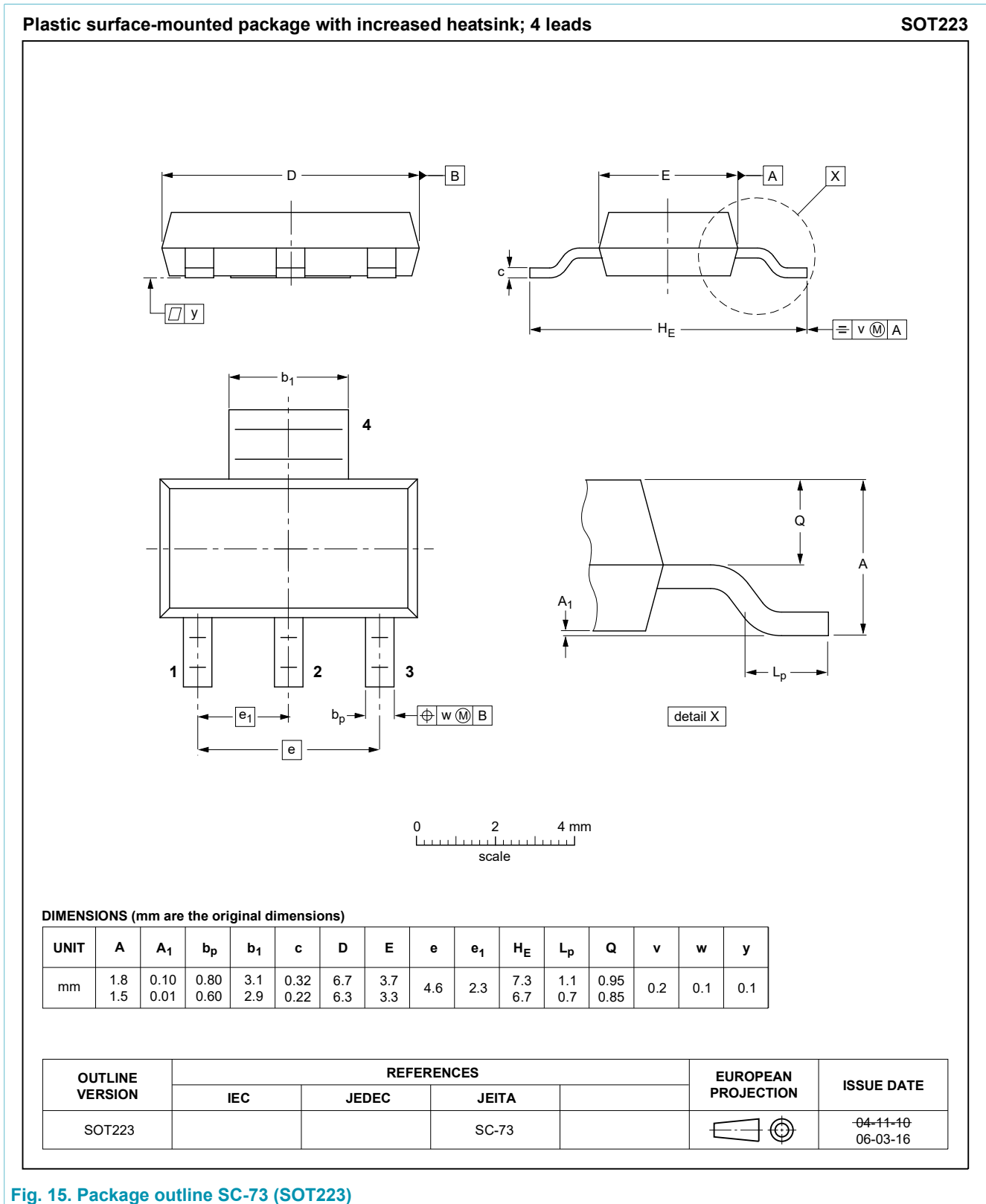


Fig. 15. Package outline SC-73 (SOT223)

## 11. Legal information

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## 12. Contents

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1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Limiting values.....	3
8. Thermal characteristics.....	6
9. Characteristics.....	8
10. Package outline.....	10
11. Legal information.....	11

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